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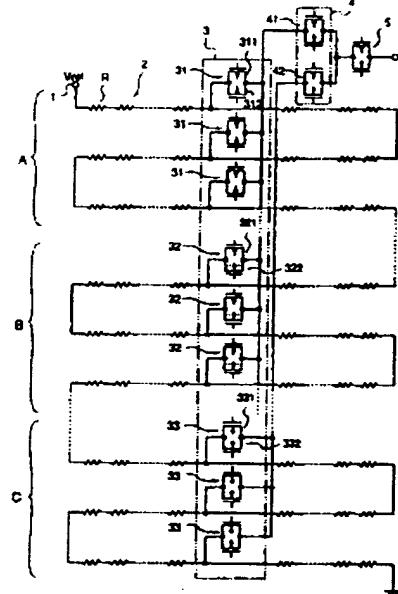
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TITLE : REFERENCE VOLTAGE CIRCUIT



ABSTRACT : PURPOSE: To improve the accuracy of a reference voltage and the operating speed by employing a P enhancement transistor(TR) for a high level transfer gate, a low threshold level N TR for a middle level transfer gate, and an N enhancement TR for a low level transfer gate.

CONSTITUTION: P enhancement TRs 311, 312 offering low ON-resistance and an N TR 322 and low threshold level N enhancement TRs 331, 332 respectively in a high level region A, a middle level region B and a low level region C are employed. Thus, a reference voltage with high accuracy is obtained for all the voltage regions.

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